

IN THE CLAIMS

1 (Currently Amended). A method comprising:
developing a patterned photoresist;
~~absorbing a plasticizer in a supercritical fluid into the surface of said patterned~~
~~photoresist after developing~~ lowering the glass transition temperature of the photoresist; and
reflowing the photoresist after lowering the glass transition temperature ~~absorbing~~
~~the plasticizer.~~

Claim 2 (Canceled).

3 (Currently Amended). The method of claim 1 including applying a [[the]]
plasticizer in a supercritical carbon dioxide fluid.

Claims 4 and 5 (Canceled).

6 (Currently Amended). The method of claim 1 including applying a [[the]]
plasticizer with the develop rinse.

7 (Original). The method of claim 1 including applying a plasticizer that improves the
etch resistance of the photoresist.

8 (Original). The method of claim 1 wherein applying a plasticizer includes diffusing a
plasticizer into the photoresist.

9 (Original). The method of claim 8 including diffusing a plasticizer in a vapor phase
into the photoresist.

10 (Original). The method of claim 1 including controlling the amount of reflow by
volatilizing the plasticizer during reflow.

11 (Original). The method of claim 1 including applying the plasticizer in liquid carbon dioxide.

12 (Original). The method of claim 1 including controlling the amount of reflow by cooling the photoresist.

Claims 13-27 (Canceled).